Passive Device Verilog Models For Board And System-Level Digital Simulation

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ABSTRACT
Board and system-level simulations require a simulation model for each component in the design. Simulation models for digital components are commercially available from LMC and Cadence, and can be readily created by in-house simulation-model groups, but some of the more difficult simulation models to acquire are the seemingly trivial passive devices that appear on a schematic. This paper details a bi-directional resistor model which is configurable from a schematic. Examples and benchmarks are included. This paper also details a configurable power supply model.

1. Introduction
While doing board-level simulation with LMC ECL simulation models at Tektronix, we experienced difficulties associated with our simple $rtran$ resistor model. Specifically, it appeared we needed different resistor models for series-termination, parallel-termination and pull-up resistor configurations.

During subsequent board-level simulations using an LMC PLD device, we discovered potential problems with our simple VCC and GND models.

Our goal was to create passive device models that were efficient, versatile, and possessed intelligent default behavior.

2. The Resistor Model
Two problems that we had experienced with earlier design tools included:

- Unidirectional resistor models - design engineers object to directional schematic resistor symbols.
- Different models for different uses - design engineers do not want to use different schematic symbols to represent pullup and termination resistors.

To address the above problems, we set the following model goals:

- One Schematic symbol for all resistor configurations.
- Bi-directional symbol and model.
- Intelligent default setting.
- If possible, faster default setting option.

3. Driving LMC ECL Gates
Figure 1 shows an example of an LMC ECL model driven with four different input strengths: $supply$, $strong$, $pull$ and $weak$, and Figure 2 shows the corresponding simulation results (using $monitor$ with $%v$ control).

Note that at time 10ns, all schematic inputs are set to 0, but the output strength of the $weak$-driven $buf$ gates is driven to a $Pu0$ strength.

Similarly at time 40ns, all schematic inputs are set to one, but the output strength of the $weak$-driven $buf$ gates is driven to a $Pu0$ strength, while the output strength of the pull-driven $buf$ gates are now at $PuX$ (due to the $Pu0$ back-drive from the LMC ECL device, conflicting with the $Pull$ drive from the $buf$ gates).

In order to successfully drive a 1 onto the LMC device, the input must at least be of $strong$ drive strength. If the input were driven through a series-termination resistor modeled as an $rtran$ device, only $pull$ strength would be presented to the LMC device inputs.
Figure 1 - LMC ECL model driven by different strengths

<table>
<thead>
<tr>
<th>Time (ns)</th>
<th>INA PORTS</th>
<th>SUPPLY BUFFERS DRIVE</th>
<th>INB PORTS</th>
<th>STRONG BUFFERS DRIVE</th>
<th>INC PORTS</th>
<th>PULL BUFFERS DRIVE</th>
<th>IND PORTS</th>
<th>WEAK BUFFERS DRIVE</th>
</tr>
</thead>
<tbody>
<tr>
<td>0.00</td>
<td>z&amp;z</td>
<td>SuX&amp;SuX</td>
<td>z&amp;z</td>
<td>StX&amp;StX</td>
<td>z&amp;z</td>
<td>PuX&amp;PuX</td>
<td>z&amp;z</td>
<td>Pu0&amp;Pu0</td>
</tr>
<tr>
<td>10.00</td>
<td>0&amp;0</td>
<td>Su0&amp;Su0</td>
<td>0&amp;0</td>
<td>St0&amp;St0</td>
<td>0&amp;0</td>
<td>Pu0&amp;Pu0</td>
<td>0&amp;0</td>
<td>Pu0&amp;Pu0</td>
</tr>
<tr>
<td>20.00</td>
<td>0&amp;1</td>
<td>Su0&amp;Su1</td>
<td>0&amp;1</td>
<td>St0&amp;St1</td>
<td>0&amp;1</td>
<td>Pu0&amp;PuX</td>
<td>0&amp;1</td>
<td>Pu0&amp;Pu0</td>
</tr>
<tr>
<td>30.00</td>
<td>1&amp;0</td>
<td>Su1&amp;Su0</td>
<td>1&amp;0</td>
<td>St1&amp;St0</td>
<td>1&amp;0</td>
<td>PuX&amp;Pu0</td>
<td>1&amp;0</td>
<td>Pu0&amp;Pu0</td>
</tr>
<tr>
<td>40.00</td>
<td>1&amp;1</td>
<td>Su1&amp;Su1</td>
<td>1&amp;1</td>
<td>St1&amp;St1</td>
<td>1&amp;1</td>
<td>PuX&amp;PuX</td>
<td>1&amp;1</td>
<td>Pu0&amp;Pu0</td>
</tr>
<tr>
<td>50.00</td>
<td>0&amp;0</td>
<td>Su0&amp;Su0</td>
<td>0&amp;0</td>
<td>St0&amp;St0</td>
<td>0&amp;0</td>
<td>Pu0&amp;Pu0</td>
<td>0&amp;0</td>
<td>Pu0&amp;Pu0</td>
</tr>
</tbody>
</table>

Figure 2 - LMC ECL input drive simulation results

4. Series Termination Resistors

Figure 3 shows the same LMC ECL device, driven through wires on the first set of inputs, through default resistors on the second set of inputs, and through resistors with attached `STRENGTH=WIRE` property on the third and fourth set of inputs.
Figure 3 - LMC ECL model with series and parallel termination resistors

<table>
<thead>
<tr>
<th>Time</th>
<th>INA</th>
<th>AOUT</th>
<th>INB</th>
<th>RB</th>
<th>BOUT</th>
<th>INC</th>
<th>RC</th>
<th>COUT</th>
<th>IND</th>
<th>RD</th>
<th>DOUT</th>
</tr>
</thead>
<tbody>
<tr>
<td>0.00ns</td>
<td>z&amp;z</td>
<td>StX</td>
<td>z&amp;z</td>
<td>Pu0&amp;Pu0</td>
<td>StX</td>
<td>z&amp;z</td>
<td>Pu0&amp;Pu0</td>
<td>StX</td>
<td>z&amp;z</td>
<td>Pu0&amp;Pu0</td>
<td>StX</td>
</tr>
<tr>
<td>4.00ns</td>
<td>z&amp;z</td>
<td>We0</td>
<td>z&amp;z</td>
<td>Pu0&amp;Pu0</td>
<td>We0</td>
<td>z&amp;z</td>
<td>Pu0&amp;Pu0</td>
<td>We0</td>
<td>z&amp;z</td>
<td>Pu0&amp;Pu0</td>
<td>We0</td>
</tr>
<tr>
<td>10.00ns</td>
<td>0&amp;0</td>
<td>We0</td>
<td>0&amp;0</td>
<td>Pu0&amp;Pu0</td>
<td>We0</td>
<td>0&amp;0</td>
<td>St0&amp;St0</td>
<td>We0</td>
<td>0&amp;0</td>
<td>St0&amp;St0</td>
<td>We0</td>
</tr>
<tr>
<td>20.00ns</td>
<td>0&amp;1</td>
<td>We0</td>
<td>0&amp;1</td>
<td>Pu0&amp;PuX</td>
<td>We0</td>
<td>0&amp;1</td>
<td>St0&amp;St1</td>
<td>We0</td>
<td>0&amp;1</td>
<td>St0&amp;St1</td>
<td>We0</td>
</tr>
<tr>
<td>30.00ns</td>
<td>1&amp;0</td>
<td>We0</td>
<td>1&amp;0</td>
<td>PuX&amp;Pu0</td>
<td>We0</td>
<td>1&amp;0</td>
<td>St1&amp;St0</td>
<td>We0</td>
<td>1&amp;0</td>
<td>St1&amp;St0</td>
<td>We0</td>
</tr>
<tr>
<td>40.00ns</td>
<td>1&amp;1</td>
<td>We0</td>
<td>1&amp;1</td>
<td>PuX&amp;PuX</td>
<td>We0</td>
<td>1&amp;1</td>
<td>St1&amp;St1</td>
<td>We0</td>
<td>1&amp;1</td>
<td>St1&amp;St1</td>
<td>We0</td>
</tr>
<tr>
<td>44.00ns</td>
<td>1&amp;1</td>
<td>St1</td>
<td>1&amp;1</td>
<td>PuX&amp;PuX</td>
<td>StX</td>
<td>1&amp;1</td>
<td>St1&amp;St1</td>
<td>St1</td>
<td>1&amp;1</td>
<td>St1&amp;St1</td>
<td>St1</td>
</tr>
<tr>
<td>50.00ns</td>
<td>0&amp;0</td>
<td>St1</td>
<td>0&amp;0</td>
<td>Pu0&amp;Pu0</td>
<td>StX</td>
<td>0&amp;0</td>
<td>St0&amp;St0</td>
<td>St1</td>
<td>0&amp;0</td>
<td>St0&amp;St0</td>
<td>St1</td>
</tr>
<tr>
<td>54.00ns</td>
<td>0&amp;0</td>
<td>We0</td>
<td>0&amp;0</td>
<td>Pu0&amp;Pu0</td>
<td>We0</td>
<td>0&amp;0</td>
<td>St0&amp;St0</td>
<td>We0</td>
<td>0&amp;0</td>
<td>St0&amp;St0</td>
<td>We0</td>
</tr>
</tbody>
</table>

Figure 4 - Resistor driven simulation results
Figure 4 shows the corresponding simulation results (using \texttt{monitor} with \%v control).

At time 40ns, all schematic inputs are set to 1, and after a 4ns propagation delay (time 44ns), the A, C and D-positive (DOUT\_P) outputs are all driving a Stl, while the B AND-gate, whose inputs were driven through default resistors, has a StX at its output (note the PuX&PuX on the B AND-gate inputs).

The \texttt{STRENGTH=WIRE} property caused the resistor model to behave like a short circuit (WIRE) between the resistor terminals; thus, allowing a strong signal to pass directly to the LMC ECL input (and dominate the Pu0 back-drive).

5. Parallel Termination Resistors

Also visible in the last example (Figure 3) is the technique for configuring parallel termination resistors.

If simple resistors, using only \texttt{rtran} Verilog primitives, had been used for the output parallel terminations, a Pul strength from the pullup would conflict with a Pu0 strength from the pulldown, and would generate a PuX any time the outputs are not driven with strong strength signals (which is the case when the LMC ECL outputs go low).

Thus parallel terminations also require unique treatment. Parallel terminations can frequently be modeled as open circuits using the \texttt{STRENGTH=OPEN} property attached to the appropriate resistors, or one of the terminations might be modeled using either the \texttt{STRENGTH=WEAK} or default \texttt{STRENGTH=PULL} resistor properties.

6. Four Different Resistor Models

We created and tested four different Verilog resistor models which could be modified by a per-instance schematic property, to emulate series- and parallel-terminations, while the default unmodified resistor model would behave like a pull-up resistor. All four models can be simplified by adding \texttt{+define+SETRPULL} to the Verilog command line. This directive, in conjunction with the coded `ifdef condition, will cause the model to be compiled with a simple \texttt{rtran} device, which is adequate for digital designs that only use pullup resistors.

6.1. \texttt{r1.v} and \texttt{r2.v} Verilog Models

The first two resistor models have an identical \texttt{WIRE} mode of operation. A \texttt{tranifl} gate is enabled if the \texttt{STRENGTH=WIRE} property is set, while the other two paths through the model are disabled.

The \texttt{PULL} mode is modeled either by using an \texttt{rtranifl} gate, or by using a \texttt{tranifl} in series with an \texttt{rtran} gate. Both provide one level of strength reduction.

The \texttt{WEAK} mode is modeled using the same idea as the \texttt{PULL} mode, except that one more \texttt{rtran} gate has been added to this path to provide two levels of strength reduction.

The \texttt{OPEN} mode is accomplished by disabling all three paths between the resistor ports.

6.2. \texttt{r3.v} Verilog Model

The \texttt{r3.v} models the \texttt{WIRE} mode by enabling all three \texttt{tranifl} gates, effectively shorting out the parallel \texttt{rtran} gates.

The \texttt{PULL} and \texttt{WEAK} modes are accomplished by turning off one or two of the enables respectfully, causing the signal flow to be directed through one or two \texttt{rtran} gates.

Just like the \texttt{r1.v} and \texttt{r2.v} models, the \texttt{OPEN} mode is accomplished by disabling all three \texttt{tranifl} gates; thereby creating an open circuit between the resistor ports.

6.3. \texttt{r4.v} Verilog Model

The \texttt{r4.v} model uses the same idea as the \texttt{r1.v} and \texttt{r2.v} models, only this time bi-directional \texttt{tran} gates are replaced by unidirectional gates.

This model was attempted at the suggestion of non-Cadence Verilog vendors, whose implementations did not yet support bi-directional Verilog switches. It was further suggested that the unidirectional gates would run much faster than the bi-directional gates.

Note: unidirectional gates could not model the \texttt{WIRE} mode, since conflicting signals would drive both ports to a StX state.
// r1.v resistor model, bi-directional, configurable from schematic.
// Use Verilog command-line option +define+SETRPULL to speedup simulation which only use pullup resistors.
module r1 (p1, p2);
inout p1, p2;
parameter STRENGTH = "PULL";
`ifdef SETRPULL
   rtran i2 (p1, p2); // PULL
`else
   reg en1, en2, en3;
   tranif1 i1 (p1,p2,en1); // WIRE
   rtranif1 i2 (p1,p2,en2); // PULL
   rtranif1 i3 (p1,px,en3); rtran i4 (px,p2); // WEAK
initial case (STRENGTH)
   "WIRE" : {en1,en2,en3} = 3'b100;
   "PULL" : {en1,en2,en3} = 3'b010;
   "WEAK" : {en1,en2,en3} = 3'b001;
   "OPEN" : {en1,en2,en3} = 3'b000;
default : begin
      `ifdef NOMSG
      `else
         $display("%m: %s strength unknown, using PULL", STRENGTH);
      `endif
      {en1,en2,en3} = 3'b010;
   end
`endif
endmodule

Figure 5 - The "r1" resistor model
/r2.v Model

// r2.v resistor model, bi-directional, configurable from schematic.
// Use Verilog command-line option +define+SETRPULL to
// speedup simulation which only use pullup resistors.
module r2 (p1, p2);
inout p1, p2;
parameter STRENGTH = "PULL";
`ifdef SETRPULL
  rtran i2 (p1, p2);                      // PULL
`else
  reg en1, en2, en3;
  tranif1 i1 (p1,p2,en1);                 // WIRE
  rtranif1 i2 (p1,py,en2); rtran i3 (py,p2); // PULL
  rtranif1 i4 (p1,px,en3); rtran i5 (px,pz); // WEAK
  rtran i6 (pz,p2);
  initial case (STRENGTH)
    "WIRE" : {en1,en2,en3} = 3'b100;
    "PULL" : {en1,en2,en3} = 3'b010;
    "WEAK" : {en1,en2,en3} = 3'b001;
    "OPEN" : {en1,en2,en3} = 3'b000;
  default : begin
    `ifdef NOMSG
    `else
    $display("%m: %s strength unknown, using PULL", STRENGTH);
    `endif
    {en1,en2,en3} = 3'b010;
  end
endcase
`endif
endmodule

Figure 6 - The "r2" resistor model
// r3.v resistor model, bi-directional, configurable from schematic.
//
// Use Verilog command-line option +define=SETRPULL to
// speedup simulation which only use pullup resistors.
module r3 (p1, p2);
inout p1, p2;
parameter STRENGTH = "PULL";
`ifdef SETRPULL
   rtran r1 (p1, p2);
`else
   reg en1, en2, en3;
   tranif1 t1 (p1,n1,en1);
   tranif1 t2 (n1,n2,en2);
   tranif1 t3 (n2,p2,en3);
   rtran r1 (n1,n2);
   rtran r2 (n2,p2);
endmodule

initial case (STRENGTH)
   "WIRE" : {en1,en2,en3} = 3'b100;
   "PULL" : {en1,en2,en3} = 3'b010;
   "WEAK" : {en1,en2,en3} = 3'b001;
   "OPEN" : {en1,en2,en3} = 3'b000;
default : begin
    `ifdef NOMSG
    `else
       $display("%m: %s strength unknown, using PULL", STRENGTH);
    `endif
    {en1,en2,en3} = 3'b010;
end
endcase

Figure 7 - The "r3" resistor model
// r4.v resistor model, bi-directional, configurable from schematic.
//
// Use Verilog command-line option +define+SETRPULL to
// speedup simulation which only use pullup resistors.
module r4 (p1, p2);
  inout p1, p2;
  parameter STRENGTH = "PULL";
  `ifdef SETRPULL
    rnmos i3 (p1, p2, 1'b1); rnmos i4 (p2, p1, 1'b1); // PULL
  `else
    reg en1, en2, en3;
    nmos  i1 (p1, p2, en1); nmos  i2 (p2, p1, en1); // WIRE
    rnmos i3 (p1, p2, en2); rnmos i4 (p2, p1, en2); // PULL
    rnmos i5 (p1, p3, en3); rnmos i6 (p3, p2, en3); // WEAK
    rnmos i7 (p2, p4, en3); rnmos i8 (p4, p1, en3);
  `endif
  initial case (STRENGTH)
    "WIRE" : {en1, en2, en3} = 3'b100;
    "PULL" : {en1, en2, en3} = 3'b010;
    "WEAK" : {en1, en2, en3} = 3'b001;
    "OPEN" : {en1, en2, en3} = 3'b000;
  default : begin
    `ifdef NOMSG
    `else
      $display("%m: %s strength unknown, using PULL", STRENGTH);
    `endif
    {en1, en2, en3} = 3'b010;
  end
  endcase
  `endif
endmodule

Figure 8 - The "r4" resistor model
7. Resistor Model Benchmarks

The four preceding resistor models were benchmarked by tying together the inputs of 2,000 resistors, and monitoring the 2,000 outputs for a few input transitions.

The 2,000-resistor simulations were conducted with attached `STRENGTH` properties, including a misspelled `STRENGTH` property (`ERR`), and with the Verilog command line `+SETRPULL` pullup default setting. The results are outlined in the table below.

<table>
<thead>
<tr>
<th>Verilog-XL 1.6b - SPARCstation2</th>
</tr>
</thead>
<tbody>
<tr>
<td>Using <code>r1.v</code> model</td>
</tr>
<tr>
<td><strong>PULL</strong></td>
</tr>
<tr>
<td>Memory usage (bytes)</td>
</tr>
<tr>
<td>Simulation events</td>
</tr>
<tr>
<td>Compile time (secs)</td>
</tr>
<tr>
<td>Link time (secs)</td>
</tr>
<tr>
<td>Simulation time (secs)</td>
</tr>
<tr>
<td><strong>Total CPU Time (secs)</strong></td>
</tr>
</tbody>
</table>

| Using `r2.v` model |
| **PULL** | **WIRE** | **WEAK** | **OPEN** | **ERR** | `+SETRPULL` |
| Memory usage (bytes) | 13,981,480 | 13,981,480 | 13,981,480 | 13,981,396 | 13,981,472 | 4,222,404 |
| Simulation events | 77,033 | 72,033 | 72,033 | 26,033 | 72,033 | 14,033 |
| Compile time (secs) | 2.5 | 2.5 | 2.5 | 2.6 | 2.6 | 2.6 |
| Link time (secs) | 53.6 | 53.7 | 53.6 | 53.6 | 53.6 | 8.1 |
| Simulation time (secs) | 32.2 | 32.1 | 32.2 | 32.6 | 32.1 | 1.2 |
| **Total CPU Time (secs)** | **88.1** | **88.1** | **88.1** | **88.8** | **88.3** | **11.9** |

| Using `r3.v` model |
| **PULL** | **WIRE** | **WEAK** | **OPEN** | **ERR** | `+SETRPULL` |
| Memory usage (bytes) | 12,645,480 | 12,645,480 | 12,645,480 | 12,645,460 | 12,645,472 | 4,222,404 |
| Simulation events | 56,033 | 54,033 | 58,033 | 24,033 | 56,033 | 14,033 |
| Compile time (secs) | 2.6 | 2.6 | 2.5 | 2.5 | 2.5 | 2.6 |
| Link time (secs) | 18.8 | 18.8 | 18.8 | 18.8 | 18.8 | 8.2 |
| Simulation time (secs) | 5.5 | 5.4 | 5.7 | 3.3 | 5.6 | 1.2 |
| **Total CPU Time (secs)** | **26.9** | **26.8** | **27.0** | **24.6** | **26.0** | **12.0** |

| Using `r4.v` model |
| **PULL** | **WIRE** | **WEAK** | **OPEN** | **ERR** | `+SETRPULL` |
| Memory usage (bytes) | 14,185,868 | 14,017,196 | 14,185,868 | 14,185,868 | 14,185,860 | 4,972,904 |
| Simulation events | 30,096 | 16,034 | 30,096 | 18,042 | 30,096 | 14,096 |
| Accelerated events | 68,059 | 24,053 | 94,059 | 30,059 | 68,059 | 33,225 |
| Compile time (secs) | 2.5 | 2.5 | 2.6 | 2.6 | 2.7 | 3.0 |
| Link time (secs) | 17.4 | 17.4 | 17.7 | 17.8 | 17.4 | 7.2 |
| Simulation time (secs) | 203.4 | 51.5 | 203.0 | 74.3 | 219.1 | 55.8 |
| **Total CPU Time (secs)** | **223.3** | **71.4** | **223.3** | **94.7** | **239.1** | **66.0** |

Figure 9 - Benchmark simulation 2000 resistors
For overall speed, the r3.v resistor model was a clear winner, and used only 6% more memory than the r1.v resistor model.

The results of the benchmark testing produced two surprises:

1. We thought that the parallel path resistor models (r1.v and r2.v) would be more efficient than the r3.v model. Such was not the case.

2. Based on information received from non-Cadence Verilog vendors, we thought that the unidirectional switch resistor model might be more efficient than the bi-directional-switch counter parts. In fact, the benchmark demonstrated that the unidirectional-switch models performed much worse. We recognize that the unidirectional-switch models may perform much better with another vendor's version of Verilog.

We also attempted to run the benchmarks with the +switchxl Verilog command line switch, but this caused our memory usage to increase to the point where the benchmark tests appeared to be memory-disk swapping, and test-run times exceeded our patience level.

In every case, using the Verilog command line switch +define+SETRPULL achieved significant speed and memory utilization improvements; therefore, if a schematic design only uses pullup-type resistors, this switch can improve simulation efficiency by deleting unnecessary logic.

8. VCC and GND Models

There are also subtle decisions to be made when creating a model for power supplies. If VCC and GND are modeled with supply drive strengths, a design with a gate output tied to either VCC or GND may simulate without error or warning, but the problematic gate may bum-up on the actual circuit board.

Conversely, modeling VCC and GND with strong strengths poses different problems as we discovered with the following example.

This LMC PLD device is programmed to be a 2-bit up/down counter and NAND gate: with inputs, GIN1, GIN2, and output GOUT.

In this circuit, our GND model drove a strong0 strength, and of the outputs of this PLD device were always unknown.

The grounded unused configurable F2, F3, F6 and F7 pins happened to be driving a Stl against the St0 GND, producing a StX, which was fed back to the OE/I19 input, and disabled all outputs.

![Figure 10 - "strong" strength GND model](image)

The apparent, simple solution is to always drive supply strengths on power and ground symbols; however, in this case, the simulation would have passed, but the device would have failed on the prototype board.

For this reason, the Tektronix supply model still drives strong outputs by default, but can be reconfigured from the Verilog command line to drive supply strengths by using the +define+SETSUPPLY0 command switch.

```
module supply(out);
    output out;
    reg outreg;
    parameter COMPONENT = 0;
    `ifdef SETSUPPLY0
        wire (supply0, supply1) out = outreg;
    `else
        wire (strong0, strong1) out = outreg;
    `endif
    initial outreg = COMPONENT;
endmodule
```

![Figure 11 - supply.v Verilog code](image)

9. Conclusions

The resistor and power supply models outlined in this paper accomplished our overall goal of creating simplified Verilog models and schematic symbols with powerful configuration options.

Other passive device Verilog models have been written, using the same behavioral/structural model controlling techniques described in this paper.
10. Revision 1.1 (November 2004) - What Changed?

The original source file for this paper had been lost so the paper was re-captured and cleaned up.

Both authors were Tektronix employees at the time the paper was first released but both have moved to new companies.

11. Author & Contact Information

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(Data accurate as of November 2nd, 2004)